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LEE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **WATANABE, et al.**

Group Art Unit: 2825

Serial No.: 09/320,271 ✓

Examiner: LEE

Filed: May 27, 1999

P.T.O. Confirmation No.: 4409

For: **SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF**

RESPONSE UNDER 37 CFR §1.116
- EXPEDITED RESPONSE -
GROUP ART UNIT 2825

BOX AF

Commissioner for Patents
Washington, D.C. 20231

March 17, 2003

Sir:

In response to the Office Action dated **December 16, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

NOT ENTERED
F17
CV

1. **(Five Times Amended)** A fabrication method of a semiconductor device comprising the steps of:
- forming a first insulation layer on a flat underlying face over a substrate,
 - introducing impurities into said first insulation layer, and
 - embedding and forming a first conductive layer in said first insulation layer by the Damascene method.